

PN3566

NPN SILICON TRANSISTOR



TO-92 CASE

**Central**  
Semiconductor Corp.

[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR PN3566 is a small signal NPN silicon transistor, manufactured by the epitaxial planar process, designed for general purpose amplifier applications where high collector current is required.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

**SYMBOL**

$V_{CBO}$	40
$V_{CEO}$	30
$V_{EBO}$	5.0
$I_C$	600
$P_D$	625
$T_J, T_{stg}$	-65 to +150
$\theta_{JA}$	200

**UNITS**

V
V
V
mA
mW
$^\circ\text{C}$
$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

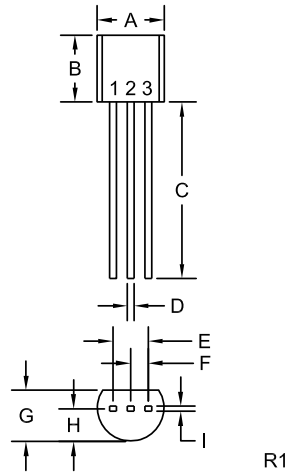
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=20\text{V}$		50	nA
$I_{EBO}$	$V_{EB}=5.0\text{V}$		10	$\mu\text{A}$
$BV_{CBO}$	$I_C=100\mu\text{A}$	40		V
$BV_{CEO}$	$I_C=30\text{mA}$	30		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.0	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$		0.9	V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=2.0\text{mA}$	80		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	150	600	
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0$		25	pF

R0 (22-July 2010)

PN3566  
NPN SILICON TRANSISTOR



**TO-92 CASE - MECHANICAL OUTLINE**



R1

**LEAD CODE:**

- 1) Emitter
- 2) Base
- 3) Collector

**MARKING:**

**FULL PART NUMBER**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

R0 (22-July 2010)